

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L1 | 2 | "10605199" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 11:35 |
| L2 | 5 | "10210031" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 11:36 |
| L3 | 2 | "6875653".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 11:42 |
| L4 | 2 | "6777737".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 11:58 |
| L5 | 6 | wang near ting-shing.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 11:59 |
| L6 | 0 | (dynamic near random near access near memory or dram) and (pillar\$1) and (substrate or wafer) and (verical near trnasistor) and (capacitor).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 12:01 |
| L7 | 0 | (dynamic near random near access near memory or dram) and (pillar\$1) and (substrate or wafer) and (verical near transistor) and (capacitor).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 12:01 |
| L8 | 158 | (dynamic near random near access near memory or dram) and (pillar\$1) and (substrate or wafer) and (vertical near transistor) and (capacitor).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:37 |
| L9 | 313 | (dynamic near random near access near memory or dram) and (pillar\$1) and (substrate or wafer) and (vertical near transistor) and (capacitor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:40 |

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|-----|------|---|---|----|----|------------------|
| L10 | 2 | 9 and (third near plate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:37 |
| L11 | 240 | 9 and (word near line) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:40 |
| L12 | 226 | 11 and (bit near line) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:40 |
| L13 | 12 | 12 and (upper near electrode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:38 |
| L14 | 1154 | (dynamic near random near access near memory or dram) and (substrate or wafer) and (vertical near transistor) and (capacitor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:40 |
| L15 | 721 | 14 and (word near line) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:40 |
| L16 | 647 | 15 and (bit near line) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 15:41 |
| L17 | 6 | 14 and (third near plate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:43 |
| L18 | 13 | 14 and (third near3 plate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 13:43 |
| L19 | 19 | 16 and (schrems) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/07 15:42 |